

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max $T_A = +25^\circ\text{C}$
-30V	65m Ω @ $V_{GS} = -10\text{V}$	-3.8A
	99m Ω @ $V_{GS} = -4.5\text{V}$	-3.0A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

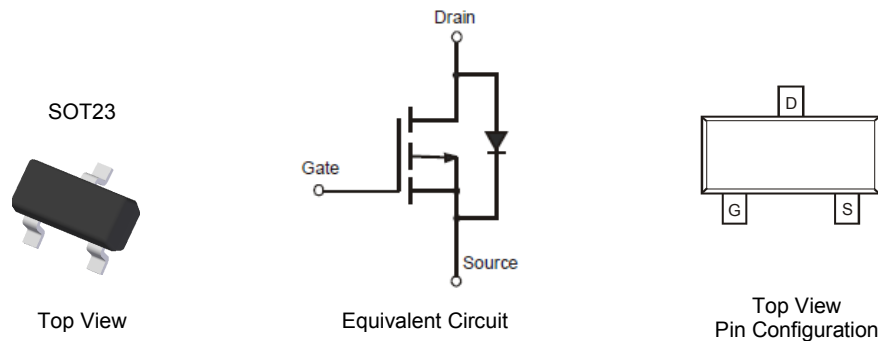
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Case: SOT23 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

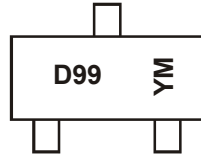


Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP3099L-7	Standard	SOT23 (Standard)	3000/Tape & Reel
DMP3099L-13	Standard	SOT23 (Standard)	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D99= Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V	I	J	K	L	M	N	O	P	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-3.8	A
		T _A = +70°C		-2.9	
Pulsed Drain Current (Note 6)			I _{DM}	-11	A

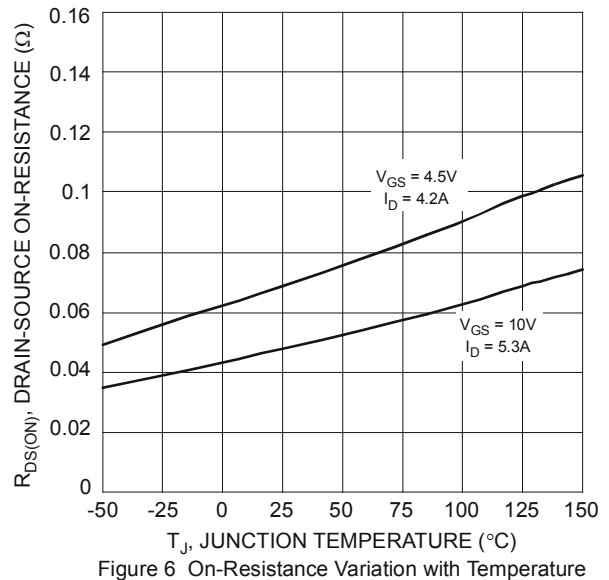
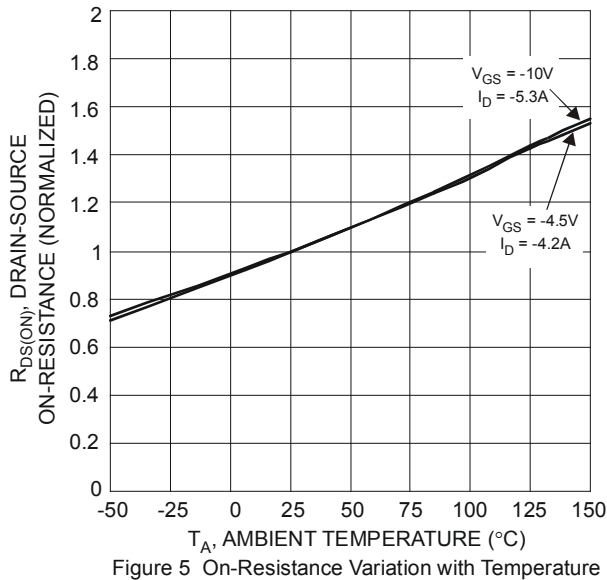
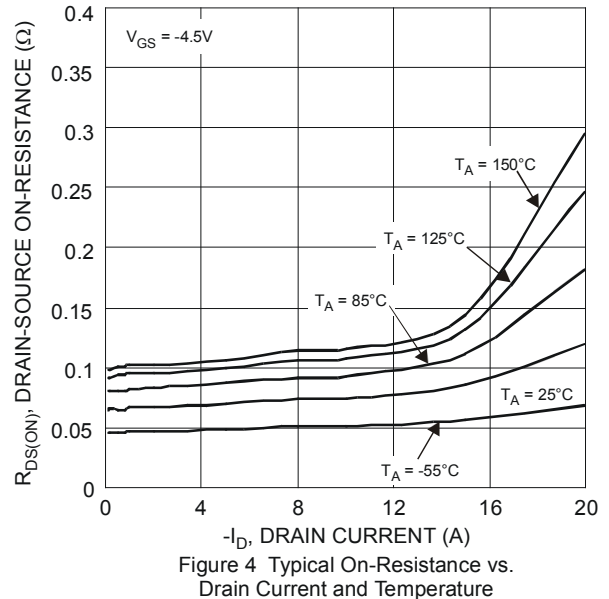
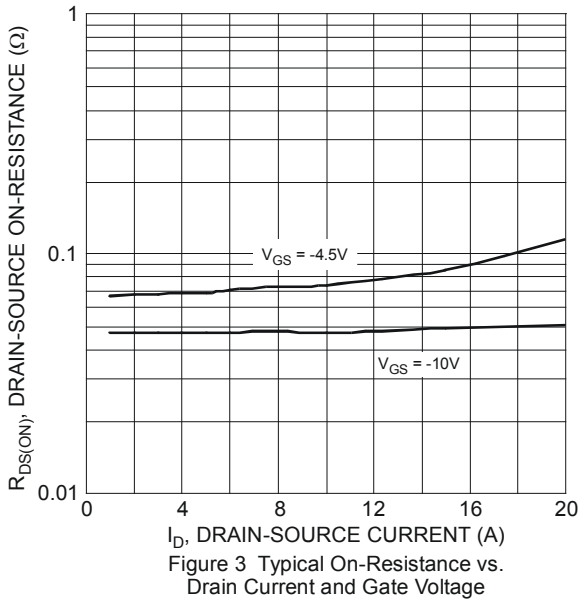
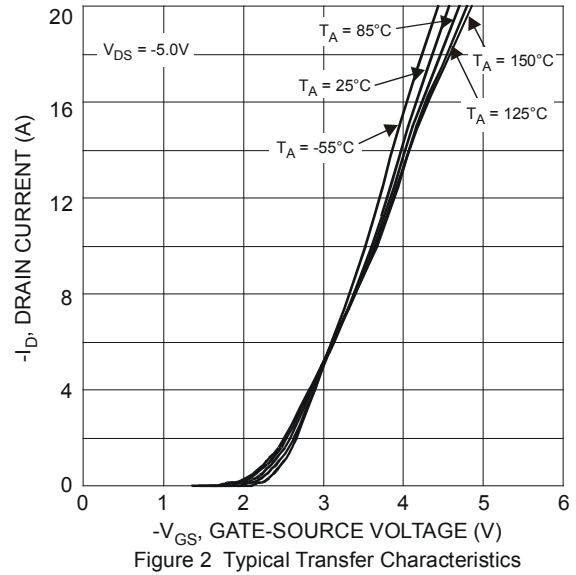
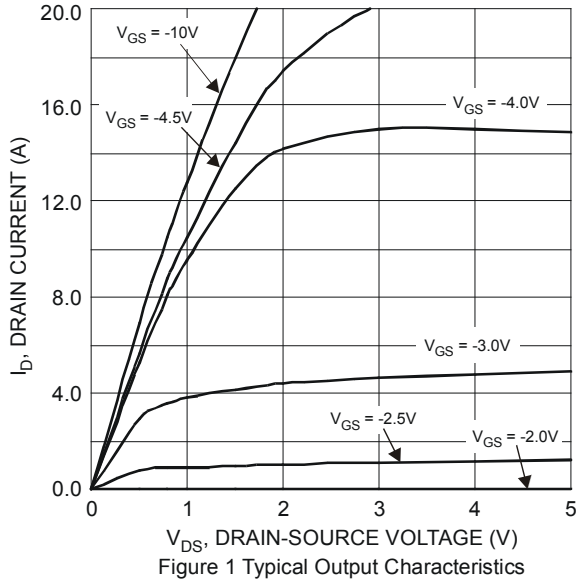
Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.08	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	115	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-800	nA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-2.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	65	mΩ	V _{GS} = -10V, I _D = -3.8A
				99		V _{GS} = -4.5V, I _D = -3.0A
Forward Transfer Admittance	Y _{fs}	—	3.6	—	S	V _{DS} = -5V, I _D = -2.7A
Diode Forward Voltage (Note 6)	V _{SD}	—	—	-1.26	V	V _{GS} = 0V, I _S = -2.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	563	—	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	48	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	41	—	pF	
Gate Resistance	R _G	—	10.3	—	Ω	V _{GS} = 0V V _{DS} = 0V, f = 1MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q _g	—	5.2	—	nC	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -3.8A
			11			V _{DS} = -15V, V _{GS} = -10V, I _D = -3.8A
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	1.9	—	—	
Turn-On Delay Time	t _{d(on)}	—	4.8	—	ns	V _{DS} = -15V, V _{GS} = -10V, I _D = -1A, R _G = 6.0Ω
Rise Time	t _r	—	5.0	—		
Turn-Off Delay Time	t _{d(off)}	—	31	—		
Fall Time	t _f	—	15	—		

- Notes:
5. Device mounted on FR-4 PCB on 2 oz., 0.5 in.² copper pads and t ≤ 5 sec.
 6. Pulse width ≤ 10μs, Duty Cycle ≤ 1%.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.



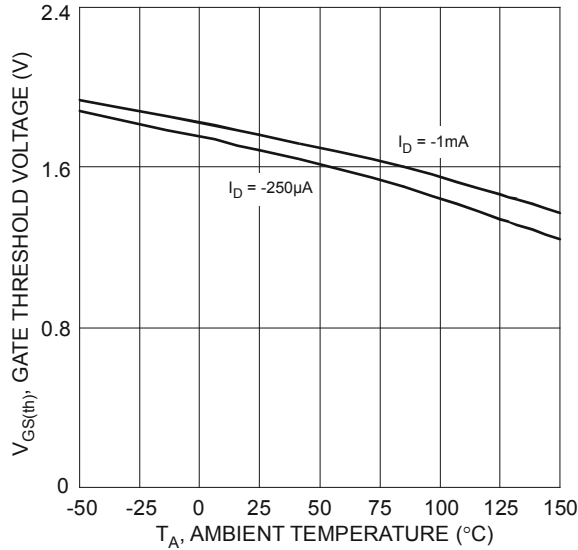


Figure 7 Gate Threshold Variation vs. Ambient Temperature

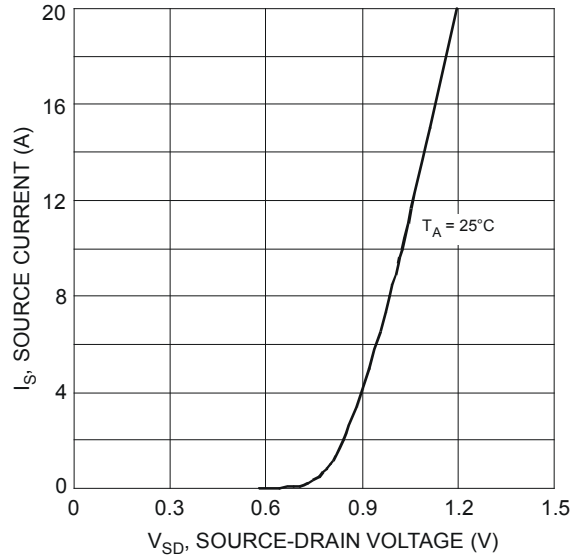


Figure 8 Diode Forward Voltage vs. Current

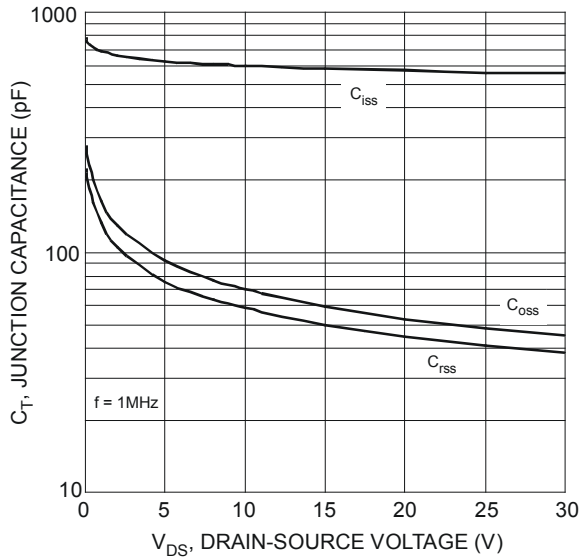


Figure 9 Typical Junction Capacitance

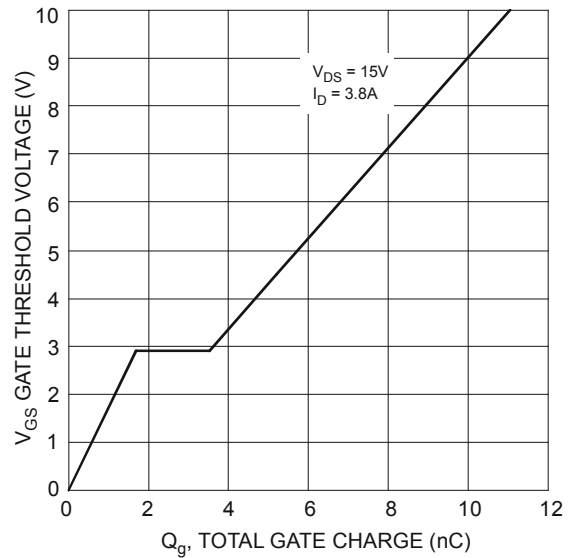
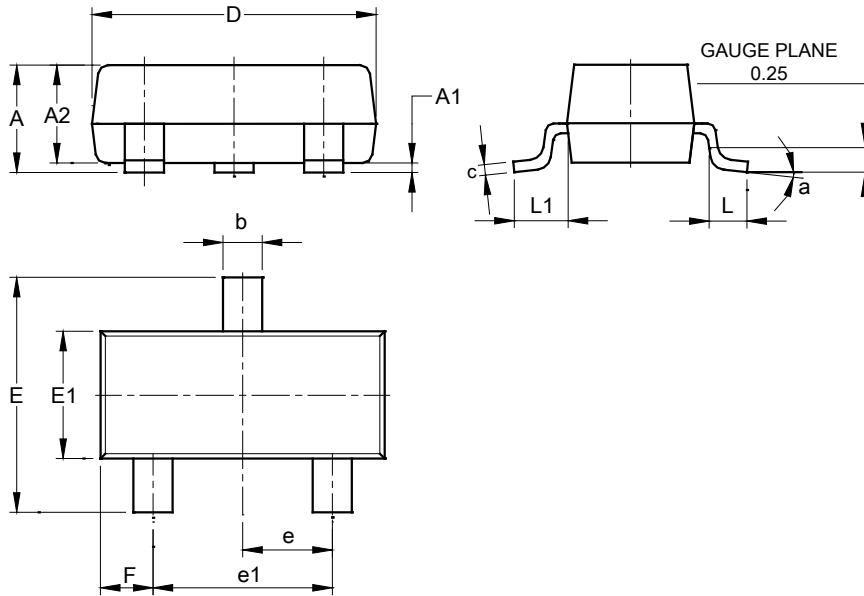


Figure 10 Gate Charge

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

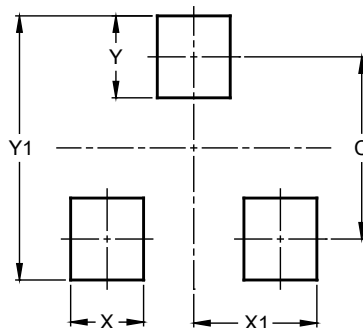


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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